

1 **IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

2 Application Serial No. .... 09/298,160  
3 Filing Date ..... April 22, 1999  
4 Inventor ..... Dan G. Custer et al.  
5 Assignee ..... Micron Technology, Inc.  
6 Group Art Unit ..... 1746  
7 Examiner ..... A. Olsen  
8 Attorney's Docket No. .... MI22-1172  
9 Title: Polishing Systems, Methods of Polishing Substrates, and Methods of Preparing  
10 Liquids for Semiconductor Fabrication Processes  
11

12 **RESPONSE TO MAY 15, 2000 OFFICE ACTION**

13 To: Assistant Commissioner for Patents  
14 Washington, D.C. 20231

15 From: Bernard Berman (Tel. 509-624-4276; Fax 509-838-3424)  
16 Wells, St. John, Roberts, Gregory & Matkin P.S.  
17 601 W. First Avenue, Suite 1300  
18 Spokane, WA 99201-3828

19 Sir:

20 **RESPONSE TO MAY 15, 2000 OFFICE ACTION**

21 To: Assistant Commissioner for Patents  
22 Washington, D.C. 20231

23 From: Bernard Berman (Tel. 509-624-4276; Fax 509-838-3424)  
Wells, St. John, Roberts, Gregory & Matkin P.S.  
601 W. First Avenue, Suite 1300  
Spokane, WA 99201-3828

Sir:

Responsive to the Office Action dated May 15, 2000, applicant requests reconsideration of the above referenced application in view of the amendments and remarks that follow [unless otherwise indicated, deletions are bracketed, additions are underlined]:

AMENDMENTS

Please amend Claim 1 as follows:

1. (Amended) A method of preparing a liquid for a semiconductor fabrication process comprising:

providing a liquid;

degassifying the liquid; [and]

injecting a gas into the liquid to regassify the liquid, the regassification increasing [increase] a total dissolved gas concentration in the liquid to greater than or equal to 200 ppb, and

employing the liquid having the increased total dissolved gas concentration for the semiconductor process.